

Product STD GPP(N side Mesa) Customer : Wai Semicorn Customer Part. No: 18100	Type 8GXNSS292-0400														
Metallization Top Nickel ① Bottom Gold ②															
Dimension in mils <table border="1"> <thead> <tr> <th></th><th>Dimension</th></tr> </thead> <tbody> <tr> <td>A</td><td>115± 2</td></tr> <tr> <td>B</td><td>88(MIN.)</td></tr> <tr> <td>C</td><td>2 (MAX.)</td></tr> <tr> <td>D</td><td>9± 1.5</td></tr> <tr> <td></td><td></td></tr> <tr> <td></td><td></td></tr> </tbody> </table>		Dimension	A	115± 2	B	88(MIN.)	C	2 (MAX.)	D	9± 1.5					
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Absolute Maximum Ratings (Ta=25?)

Electrical Characteristics					
Item	Symbol	Test Condition	Min.	Max.	Remark
FORWARD VOLTAGE	VF	IF=6A		0.97 V	Sample size 50 ea / 1lot
REVERSE CURRENT	IR	VR=400V		1μA	
BREAKDOWN VOLTAGE	BVR	IR=5μA	440V		
REVERSE RECOVERY TIME	TRR	RG1	1200ns		
TOTAL ELEC.YIELD (CHIP TEST)	BVR/VF/IR		98%		

Dice yield within wafer>90%